

Title: SEMICONDUCTOR DEVICE AND METHOD
OF MANUFACTURING THE SAME

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REPLACEMENT SHEET



11/12

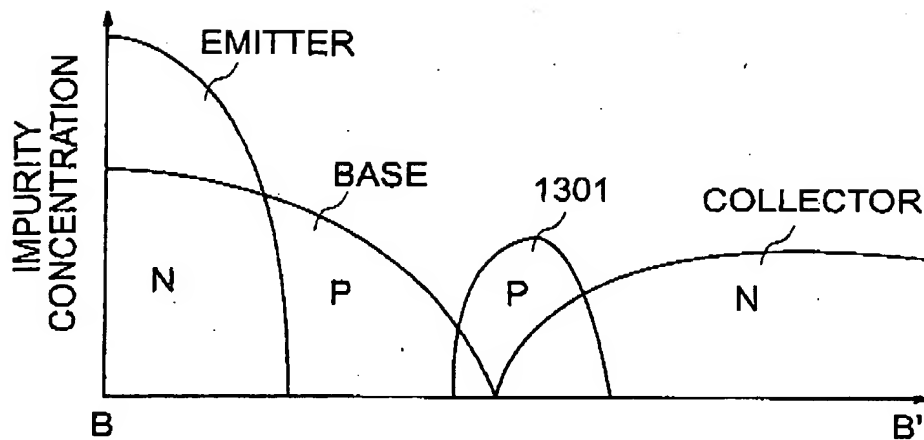


FIG. 12
PRIOR ART

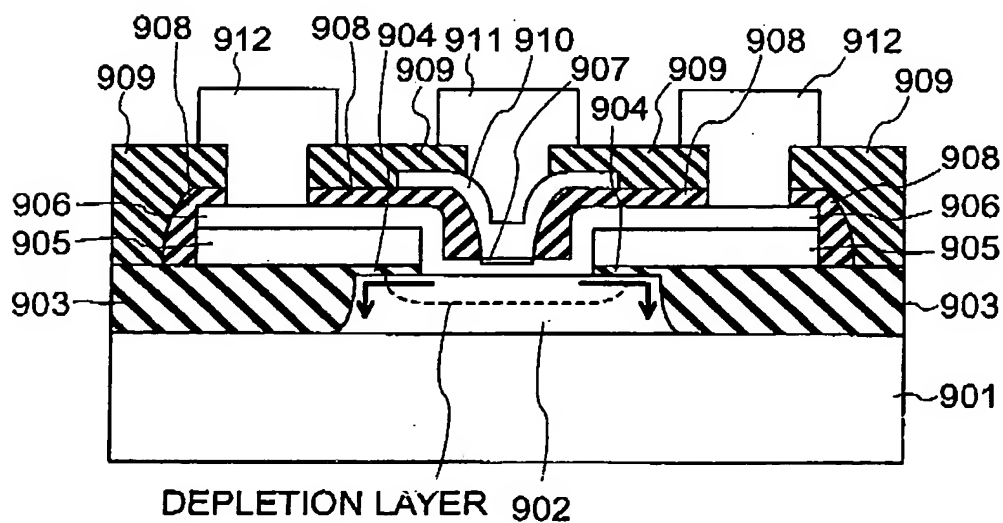


FIG. 13
PRIOR ART



A cross-sectional view of a semiconductor device. The structure consists of a substrate 901, a base layer 902, and a top layer 903. A central connection structure 904 is formed, with a central core 906 and a surrounding layer 905. The connection structure is flanked by two side structures 908, each containing a central core 909 and a surrounding layer 910. The top layer 903 is patterned to form a series of rectangular blocks 912. The connection structure 904 is shown with a wavy line indicating a transition or interface. The label "CONNECTION PARASITIC RESISTANCE" is placed below the connection structure, with a line pointing to the interface between the connection structure and the base layer 902.

FIG. 14
PRIOR ART